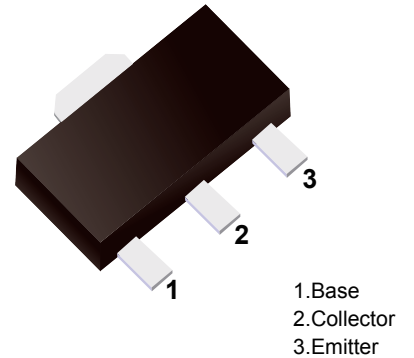


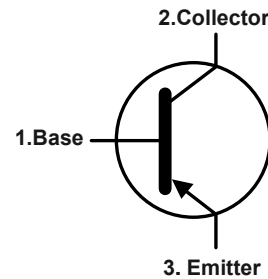
■ PNP Transistor

■ Features

- For Switching and Amplifier Applications.
- As Complementary Type of the NPN Transistor PXT8050 is Recommended.



■ Simplified outline(SOT-89)



■ Absolute Maximum Ratings Ta = 25°C

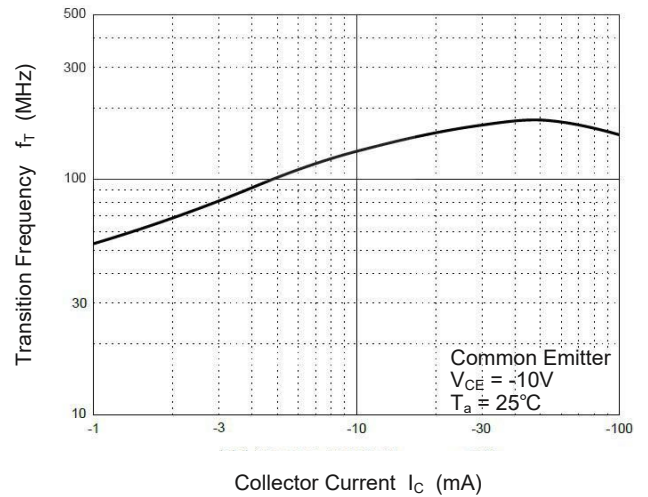
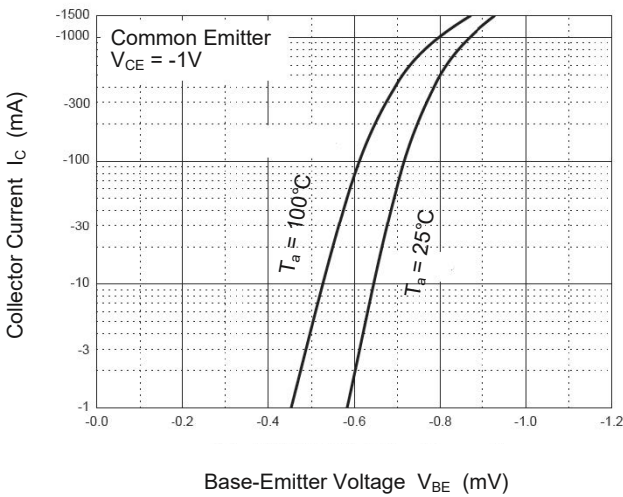
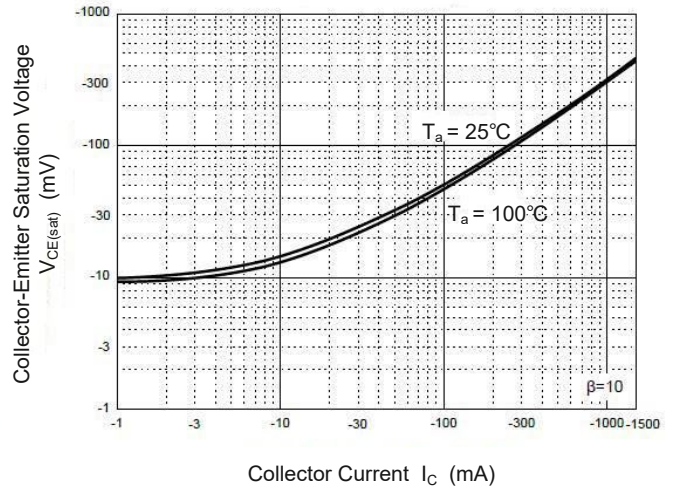
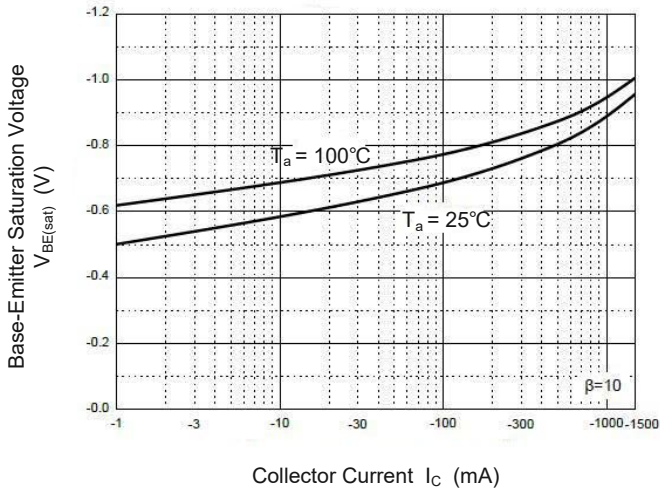
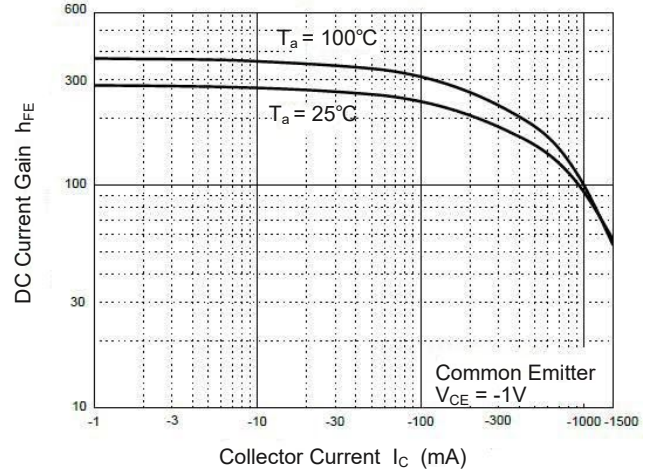
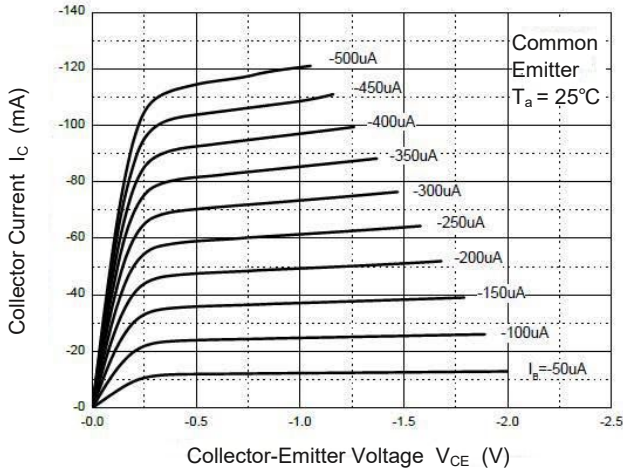
Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CB0}$	40	V
Collector Emitter Voltage	$-V_{CEO}$	25	V
Emitter Base Voltage	$-V_{EB0}$	6	V
Collector Current	$-I_C$	1.5	A
Maximum Power Dissipation	$P_D$	1	W
Junction Temperature	$T_J$	150	°C
Storage Temperature Range	$T_{STG}$	-55 to +150	°C

■ Classification of hfe(1)

Type	PXT8550
Range	200-350
Marking	Y2

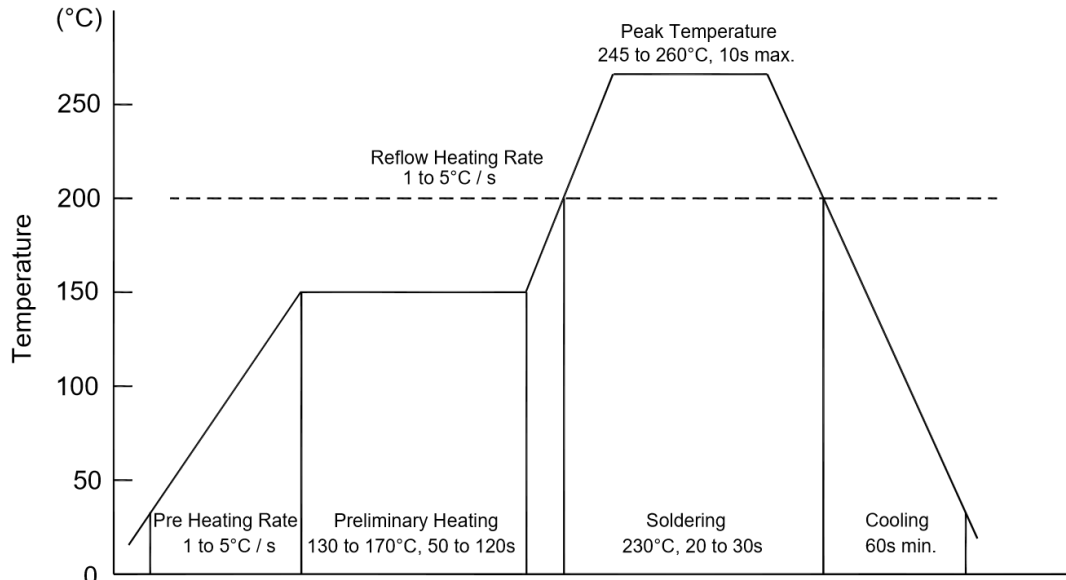
**■ Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = -1\text{ V}$ , $I_C = -100\text{ mA}$ Current Gain Group at $V_{CE} = -1\text{ V}$ , $I_C = -800\text{ mA}$	$H_{FE}$	200	--	350	--
Collector Base Cutoff Current at $V_{CB} = -40\text{ V}$	$-I_{CBO}$	--	--	100	nA
Collector Base Breakdown Voltage at $I_C = -100\text{ }\mu\text{A}$	$-V_{(BR)CBO}$	40	--	--	V
Collector Emitter Breakdown Voltage at $I_C = -0.1\text{ mA}$	$-V_{(BR)CEO}$	25	--	--	V
Emitter Base Breakdown Voltage at $I_E = -100\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	6	--	--	V
Collector Emitter Saturation Voltage at $I_C = -800\text{ mA}$ , $I_B = -80\text{ mA}$	$-V_{CE(sat)}$	--	--	0.5	V
Base Emitter Saturation Voltage at $I_C = -800\text{ mA}$ , $I_B = -80\text{ mA}$	$-V_{BE(sat)}$	--	--	1.2	V
Transition Frequency at $V_{CE} = -10\text{ V}$ , $I_C = -50\text{ mA}$	$F_T$	100	--	--	MHz



## Conditions of Soldering and Storage

### ◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

### ◆ Conditions of hand soldering

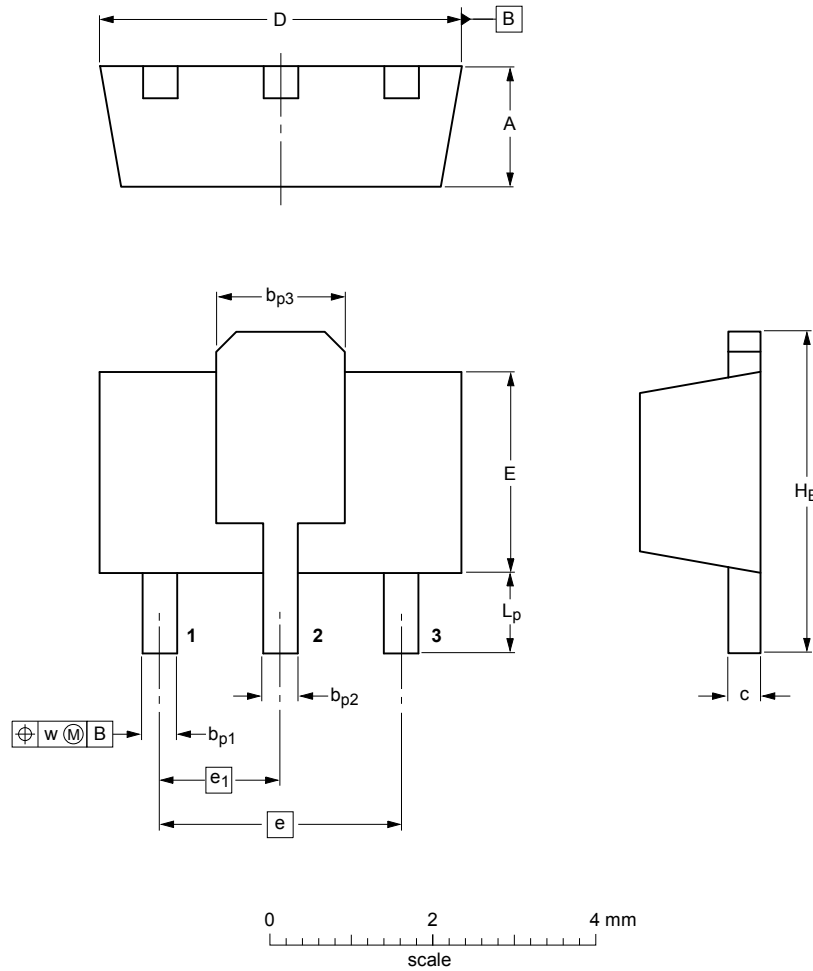
- Temperature: 370 °C
- Time: 3s max.
- Times: one time

### ◆ Storage conditions

- **Temperature**  
5 to 40 °C
- **Humidity**  
30 to 80% RH
- **Recommended period**  
One year after manufacturing

Package Outline

SOT-89



**DIMENSIONS (mm are the original dimensions)**

UNIT	A	$b_{p1}$	$b_{p2}$	$b_{p3}$	c	D	E	e	$e_1$	$H_E$	$L_p$	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13

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